

**Description**

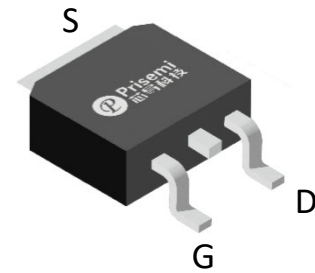
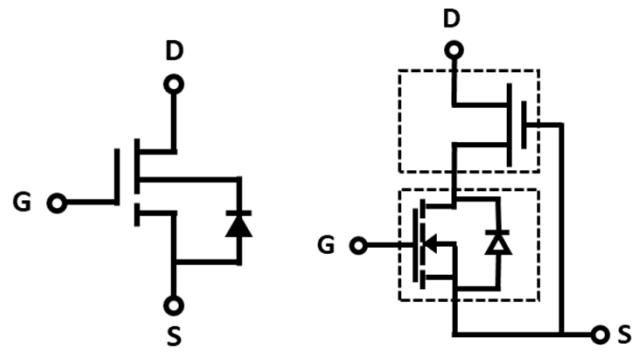
Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)(Typ)$	$I_D(A)$
700	180	12.8

**Feature**

- Easy to use, compatible with standard gate drivers
- Excellent  $Q_G \times R_{DS(on)}$  figure of merit (FOM)
- Low  $Q_{RR}$ , no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free

**Applications**

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors


**TO-252 (Top View)**

**Schematic Symbol**
**Cascode Device Structure**
**Absolute maximum rating@25°C**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	700	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Transient Drain-Source Voltage <sup>1)</sup>	$V_{TDS}$	800	V
Continuous Drain Current	$I_D$	$T_C=25^\circ C$	12.8
		$T_C=100^\circ C$	8.5
Pulsed Drain Current (Pulse Width: 100 $\mu s$ )	$I_{DM}$	$T_C=25^\circ C$	28
		$T_C=150^\circ C$	20
Power Dissipation	$P_D$	54	W
Soldering Peak Temperature	$T_{CSOLD}$	260	$^\circ C$
Operating Junction and Storage Temperature	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Resistance**

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	-	2.3	-	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient <sup>2)</sup>	$R_{\theta JA}$	-	50	-	$^\circ C/W$

## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units		
<b>Statistic Characteristics</b>								
Maximum Drain-Source Voltage	$V_{DS-Max}$	$V_{GS} = 0V$	700	-	-	V		
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	-	1000	-	V		
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=700V,$ $V_{GS}=0V$	$T_J=25^\circ C$	-	8	20	$\mu A$	
			$T_J=150^\circ C$	-	50	-		
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 150$	nA		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 500\mu A$	3	4	5	V		
Gate threshold voltage temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	-10.7	-	mV/°C		
Drain-Source On-State Resistance <sup>3)</sup>	$R_{DS(ON)}$	$V_{GS}=12V,$ $I_D=4A$	$T_J=25^\circ C$	-	180	225	mΩ	
			$T_J=150^\circ C$	-	360	-		
<b>Dynamic Characteristics</b>								
Input Capacitance	$C_{iss}$	$V_{DS} = 400V, V_{GS} = 0V,$ $f = 1MHz$	-	502	-	pF		
Output Capacitance	$C_{oss}$		-	21	-			
Reverse Transfer Capacitance	$C_{rss}$		-	1.5	-			
Effective Output Capacitance, Energy Related	$C_{o(er)}$	$V_{GS} = 0V,$ $V_{DS} = 0-400V$	-	31	-	pF		
Effective Output Capacitance, Time Related	$C_{o(tr)}$		-	65	-			
Output Charge	$Q_{oss}$		-	26	-		nC	
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 400V, I_D = 8A,$ $V_{GS} = 0-12V, R_G = 47\Omega$	-	37	-	ns		
Turn-on Rise Time	$t_r$		-	13	-			
Turn-Off Delay Time	$t_{d(off)}$		-	73	-			
Turn-Off Fall Time	$t_f$		-	8	-			
Total Gate Charge	$Q_g$	$V_{DS} = 400V, I_D = 8A,$ $V_{GS} = 0-12V$	-	15.8	-	nC		
Gate-Source Charge	$Q_{gs}$		-	3.8	-			
Gate-Drain Charge	$Q_{gd}$		-	5.5	-			
<b>Reverse Diode Characteristics</b>								
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=4A$	-	1.4	-	V		
			$V_{GS}=0V,$ $I_S=6A$	$T_J=25^\circ C$	-		2.1	-
				$T_J=150^\circ C$	-		3.2	-
Reverse Recovery Time	$t_{rr}$	$V_{GS}=0V, I_S=8A,$ $V_{DD}=400V,$ $di/dt=1000A/\mu s$	-	18	-	ns		
Reverse Recovery Charge	$Q_{rr}$		-	26	-	$\mu C$		

## Notes:

- Off-state spike duty cycle < 0.01, spike duration < 2 $\mu s$
- Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm<sup>2</sup>copper area and 70 $\mu m$  thickness)
- Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

## Typical Characteristics

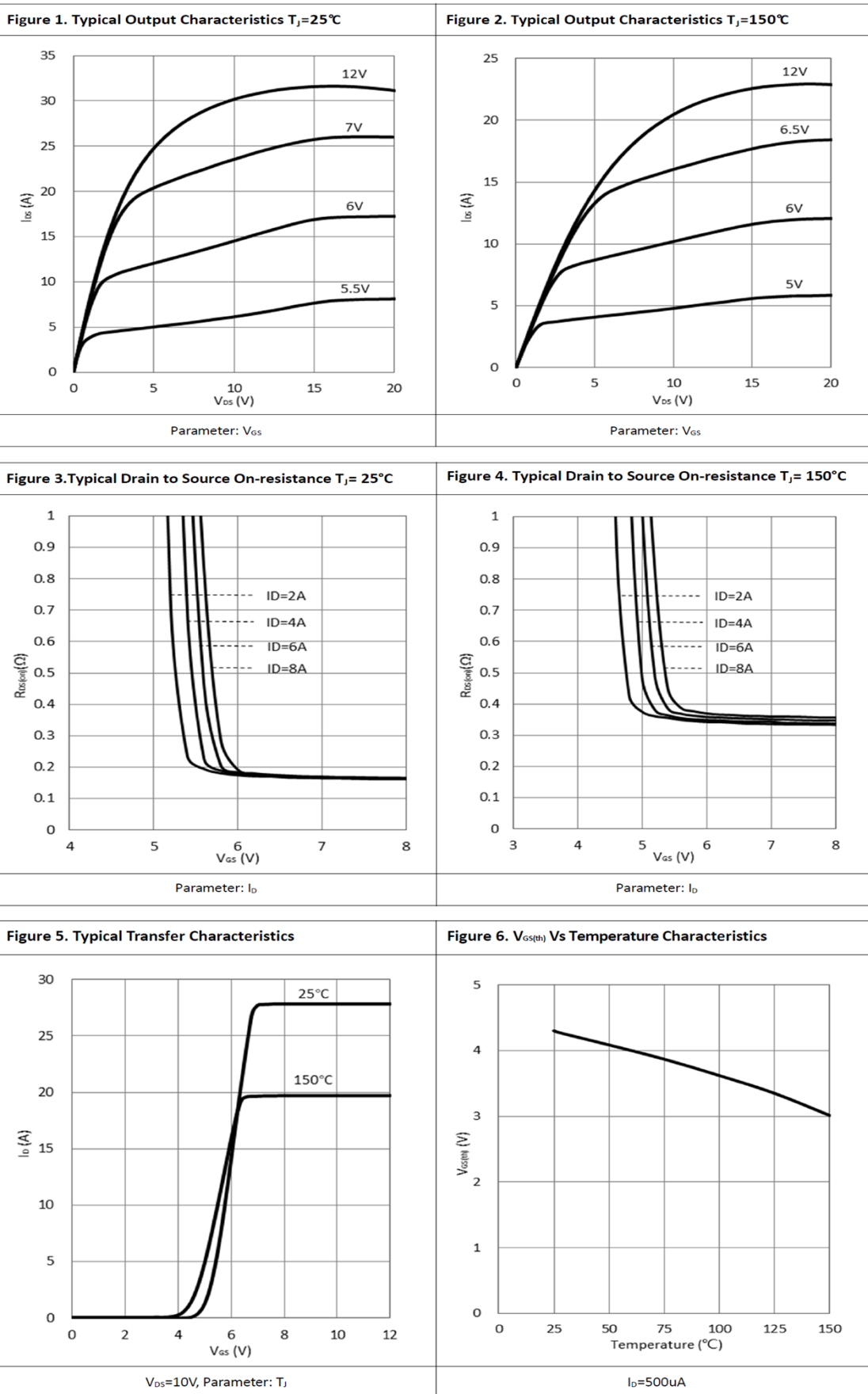
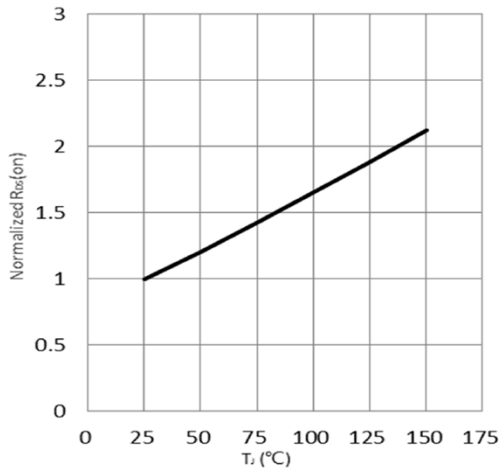
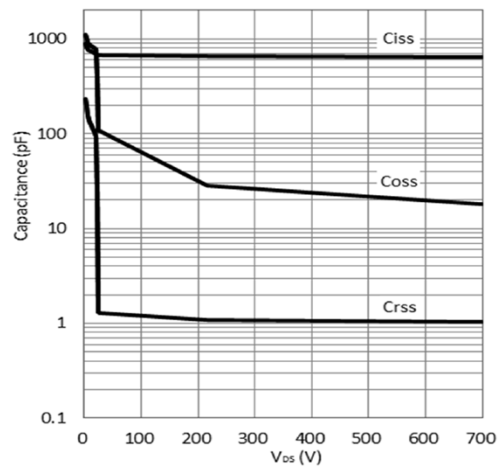


Figure 7. Normalized On-resistance



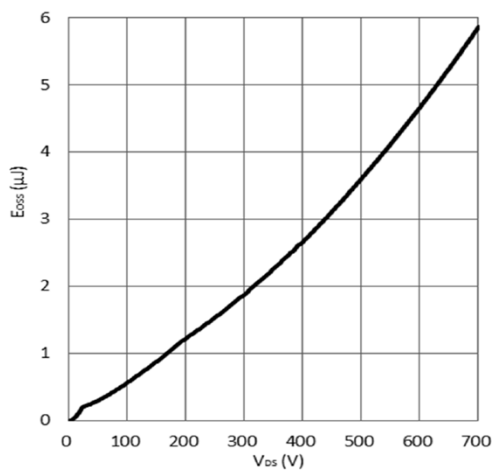
$I_D=4A, V_{GS}=12V$

Figure 8. Typical Capacitance



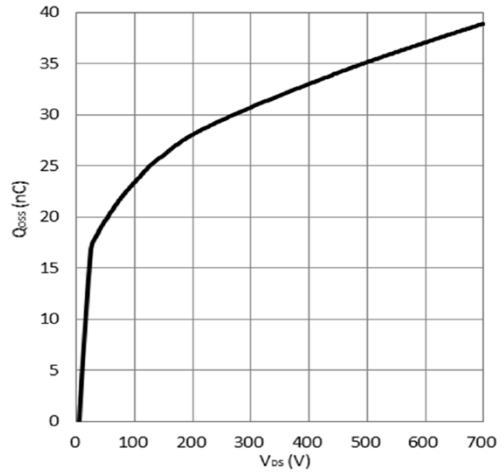
$V_{GS}=0V, f=1MHz$

Figure 9. Typical  $C_{oss}$  Stored Energy



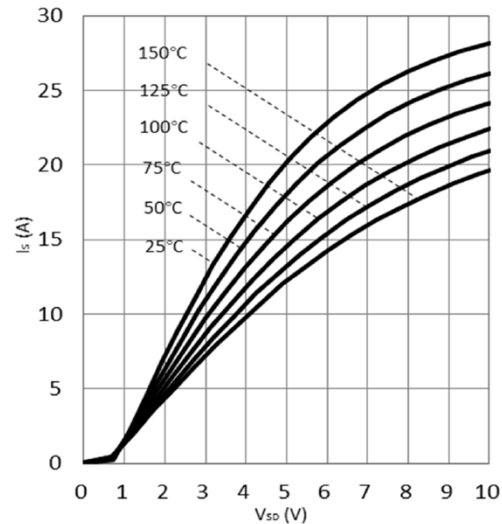
$V_{GS}=0V, f=1MHz$

Figure 10. Typical  $Q_{oss}$



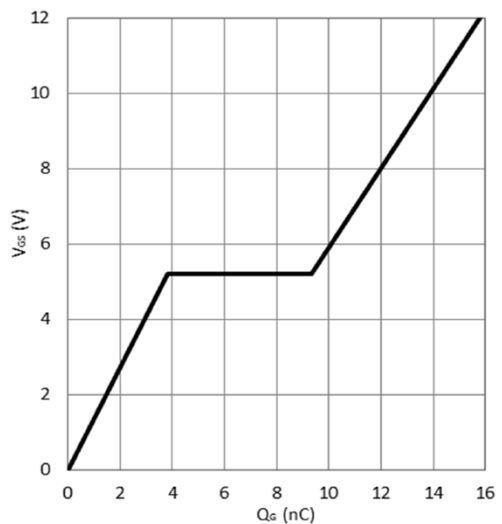
$V_{GS}=0V, f=1MHz$

Figure 11. Forward Characteristic of Rev. Diode



$I_S=f(V_{SD}),$  Parameter  $T_j$

Figure 12. Typical Gate Charge



$I_{DS}=6A, V_{DS}=400V$

Figure 13. Power Dissipation

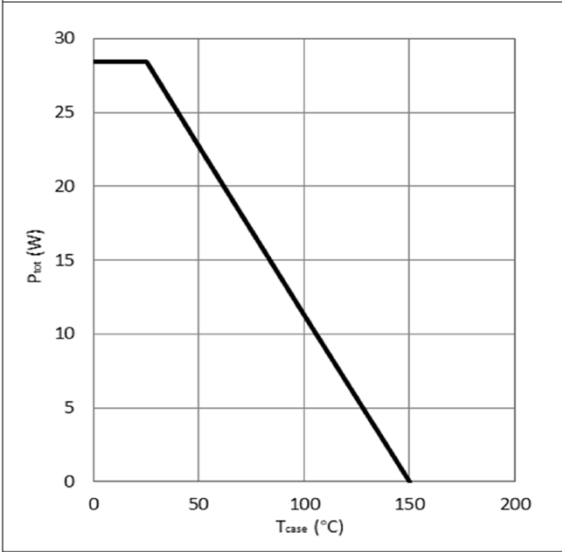


Figure 14. Current Derating

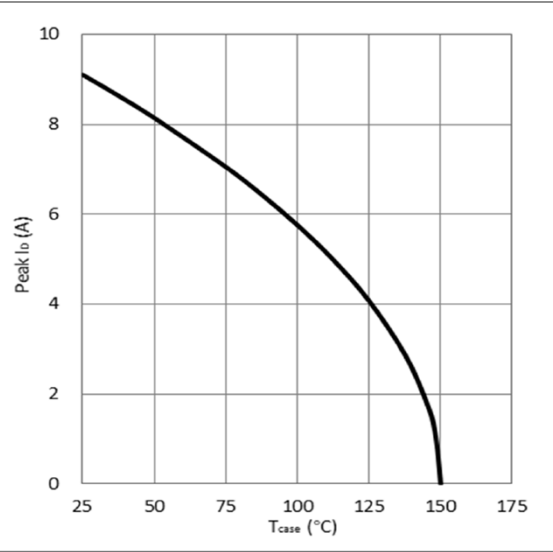


Figure 15. Transient Thermal Resistance

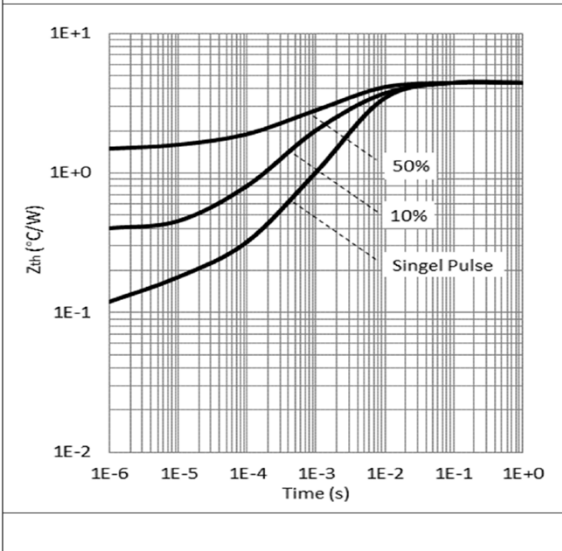


Figure 16. Safe Operating Area  $T_c=25^{\circ}$ C

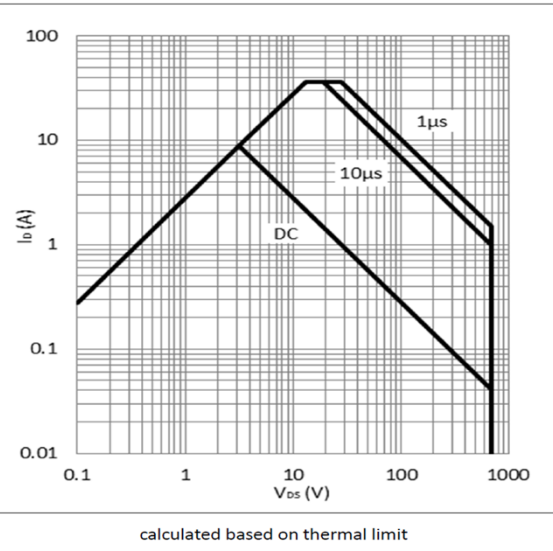
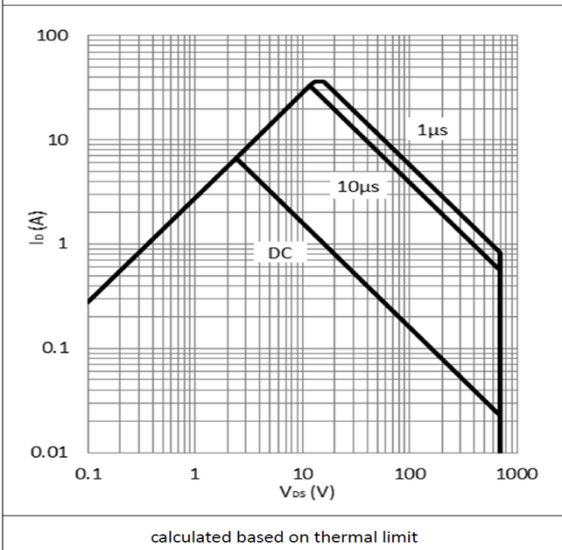


Figure 17. Safe Operating Area  $T_c=80^{\circ}$ C



Test Circuits and Waveforms

Figure 18. Switching Time Test Circuit

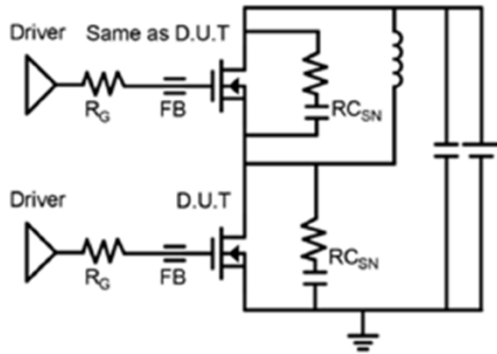


Figure 19. Switching Time Waveform

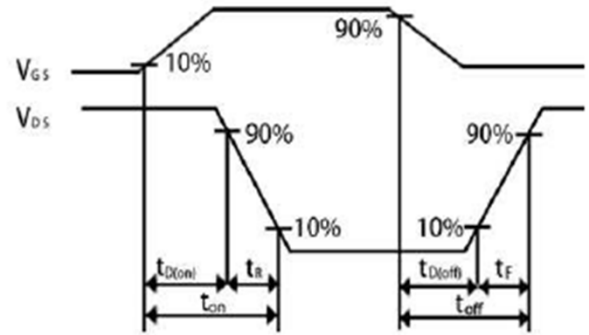


Figure 20. Dynamic  $R_{DS(on)}$  Test Circuit

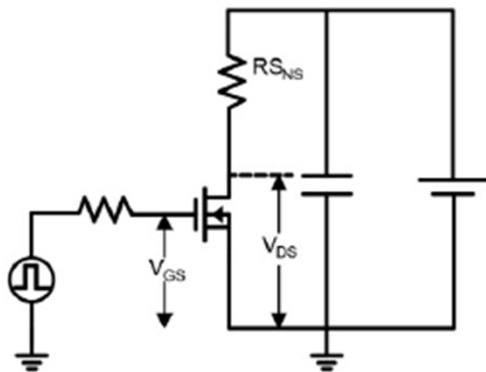


Figure 21. Dynamic  $R_{DS(on)}$  Waveform

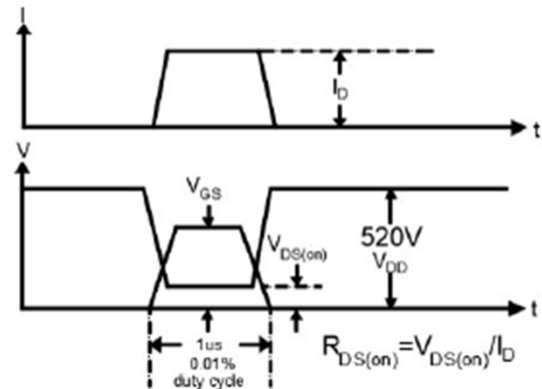


Figure 22. Diode Characteristic Test Circuits

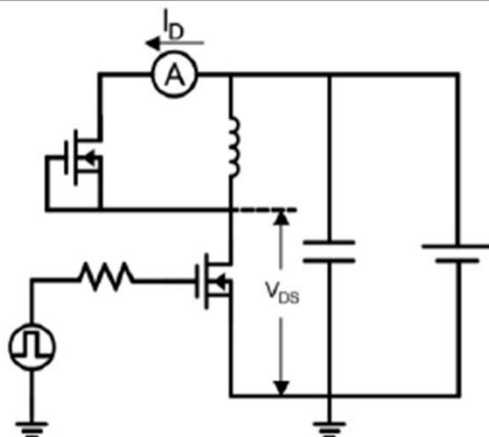
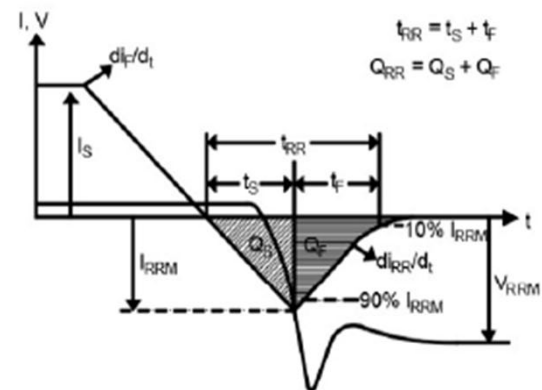
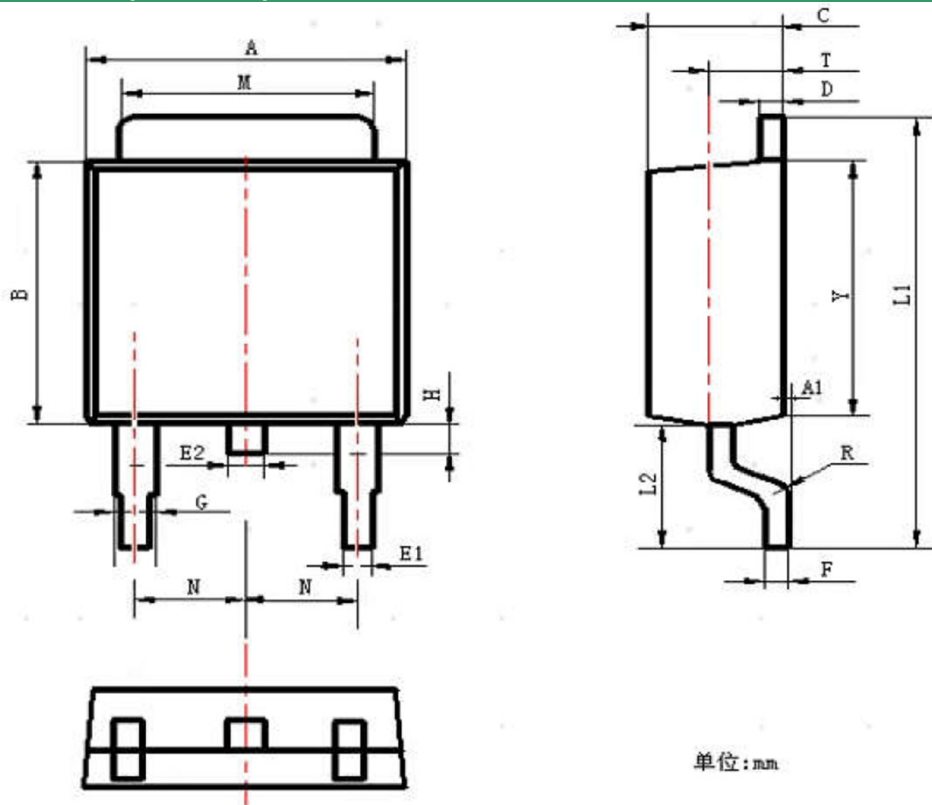


Figure 23. Diode Recovery Waveform




Product Dimension (TO-252)



SYMBOL	Millimeter	
	Min	Max
A	6.30	6.90
A1	0	0.16
B	5.70	6.30
C	2.10	2.50
D	0.30	0.90
E1	0.60	0.90
F	0.30	0.60
G	0.70	1.20
L1	9.30	10.50
L2	2.50	3.10
H	0.40	1.05
M	4.90	5.60
N	2.09	2.49


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